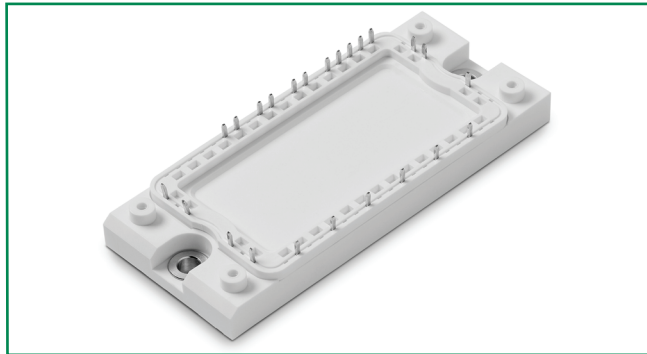


MG1215H-XBN2MM

RoHS



Features

- High level of integration—only one power semiconductor module required for the whole drive
- Low saturation voltage and positive temperature coefficient
- Fast switching and short tail current
- Free wheeling diodes with fast and soft reverse recovery
- Industry standard package with insulated copper base plate and soldering pins for PCB mounting
- Temperature sense included

Applications

- AC motor control
- Motion/servo control
- Inverter and power supplies

Module Characteristics ($T_j = 25^\circ\text{C}$, unless otherwise specified)

| Symbol | Parameters | Test Conditions | Min | Typ | Max | Unit |
|-------------------|----------------------------|---------------------|-----|------|-----|------------------|
| $T_{j\max}$ | Max. Junction Temperature | | | | 150 | $^\circ\text{C}$ |
| $T_{j\text{op}}$ | Operating Temperature | | -40 | | 125 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature | | -40 | | 125 | $^\circ\text{C}$ |
| V_{isol} | Insulation Test Voltage | AC, $t=1\text{min}$ | | 3000 | | V |
| CTI | Comparative Tracking Index | | 250 | | | |
| M_d | Mounting Torque | Recommended (M5) | 2.5 | | 5 | N·m |
| Weight | | | | 180 | | g |

Absolute Maximum Ratings ($T_j = 25^\circ\text{C}$, unless otherwise specified)

| Symbol | Parameters | Test Conditions | Values | Unit |
|--------------------|-----------------------------------|---|----------|----------------------|
| IGBT | | | | |
| V_{CES} | Collector - Emitter Voltage | $T_j=25^\circ\text{C}$ | 1200 | V |
| V_{GES} | Gate - Emitter Voltage | | ± 20 | V |
| I_C | DC Collector Current | $T_c=25^\circ\text{C}$ | 25 | A |
| | | $T_c=80^\circ\text{C}$ | 15 | A |
| I_{CM} | Repetitive Peak Collector Current | $t_p=1\text{ms}$ | 30 | A |
| P_{tot} | Power Dissipation Per IGBT | | 105 | W |
| Diode | | | | |
| V_{RRM} | Repetitive Reverse Voltage | $T_j=25^\circ\text{C}$ | 1200 | V |
| $I_{\text{F(AV)}}$ | Average Forward Current | $T_c=25^\circ\text{C}$ | 15 | A |
| I_{FRM} | Repetitive Peak Forward Current | $t_p=1\text{ms}$ | 30 | A |
| I^2t | | $T_j=125^\circ\text{C}$, $t=10\text{ms}$, $V_R=0\text{V}$ | 60 | A^2s |

Electrical and Thermal Specifications ($T_J = 25^\circ\text{C}$, unless otherwise specified)

| Symbol | Parameters | Test Conditions | Min | Typ | Max | Unit |
|---------------|---|---|-------------------------|------|------|---------------|
| IGBT | | | | | | |
| $V_{GE(th)}$ | Gate - Emitter Threshold Voltage | $V_{CE}=V_{GE}, I_C=0.6\text{mA}$ | 5.0 | 5.8 | 6.5 | V |
| $V_{CE(sat)}$ | Collector - Emitter | $I_C=15\text{A}, V_{GE}=15\text{V}, T_J=25^\circ\text{C}$ | | 1.7 | 2.15 | V |
| | Saturation Voltage | $I_C=15\text{A}, V_{GE}=15\text{V}, T_J=125^\circ\text{C}$ | | 1.9 | | V |
| I_{ICES} | Collector Leakage Current | $V_{CE}=1200\text{V}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$ | | | 0.1 | mA |
| | | $V_{CE}=1200\text{V}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$ | | | 1 | mA |
| I_{GES} | Gate Leakage Current | $V_{CE}=0\text{V}, V_{GE}=\pm 15\text{V}, T_J=125^\circ\text{C}$ | -400 | | 400 | nA |
| R_{Gint} | Integrated Gate Resistor | | | 0 | | Ω |
| Q_{ge} | Gate Charge | $V_{CE}=600\text{V}, I_C=15\text{A}, V_{GE}=\pm 15\text{V}$ | | 0.15 | | μC |
| C_{ies} | Input Capacitance | $V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$ | | 1.1 | | nF |
| C_{res} | Reverse Transfer Capacitance | | | 0.04 | | nF |
| $t_{d(on)}$ | Turn - on Delay Time | $V_{CC}=600\text{V}$ $I_C=15\text{A}$ $R_G=75\Omega$ $V_{GE}=\pm 15\text{V}$ Inductive Load | $T_J=25^\circ\text{C}$ | 90 | | ns |
| | | | $T_J=125^\circ\text{C}$ | 90 | | ns |
| t_r | Rise Time | | $T_J=25^\circ\text{C}$ | 30 | | ns |
| | | | $T_J=125^\circ\text{C}$ | 50 | | ns |
| $t_{d(off)}$ | Turn - off Delay Time | | $T_J=25^\circ\text{C}$ | 420 | | ns |
| | | | $T_J=125^\circ\text{C}$ | 520 | | ns |
| t_f | Fall Time | | $T_J=25^\circ\text{C}$ | 70 | | ns |
| | | | $T_J=125^\circ\text{C}$ | 90 | | ns |
| E_{on} | Turn - on Energy | | $T_J=25^\circ\text{C}$ | 1.5 | | mJ |
| | | | $T_J=125^\circ\text{C}$ | 2.1 | | mJ |
| E_{off} | Turn - off Energy | $T_J=25^\circ\text{C}$ | 1.1 | | mJ | |
| | | $T_J=125^\circ\text{C}$ | 1.3 | | mJ | |
| I_{SC} | Short Circuit Current | $t_{psc} \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_J=125^\circ\text{C}, V_{CC}=900\text{V}$ | | 60 | | A |
| R_{thJC} | Junction-to-Case Thermal Resistance (Per IGBT) | | | | 1.2 | K/W |
| Diode | | | | | | |
| V_F | Forward Voltage | $I_F=15\text{A}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$ | | 1.65 | 2.15 | V |
| | | $I_F=15\text{A}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$ | | 1.65 | | V |
| t_{RR} | Reverse Recovery Time | $I_F=15\text{A}, V_R=600\text{V}$ $di_p/dt=-400\text{A}/\mu\text{s}$ $T_J=125^\circ\text{C}$ | | 150 | | ns |
| I_{RRM} | Max. Reverse Recovery Current | | | 16 | | A |
| E_{rec} | Reverse Recovery Energy | | | 1.1 | | mJ |
| R_{thJCD} | Junction-to-Case Thermal Resistance (Per Diode) | | | | 1.5 | K/W |

Diode-Rectifier Absolute Maximum Ratings ($T_J = 25^\circ\text{C}$, unless otherwise specified)

| Symbol | Parameters | Test Conditions | Values | Unit |
|--------------|--------------------------------------|--|--------|----------------------|
| V_{RRM} | Repetitive Reverse Voltage | $T_J = 25^\circ\text{C}$ | 1600 | V |
| $I_{F(RMS)}$ | R.M.S. Forward Current Per Diode | $T_C = 80^\circ\text{C}$ | 50 | A |
| I_{FSM} | Non-Repetitive Surge Forward Current | $T_J = 45^\circ\text{C}$, $t = 10\text{ms}$, 50Hz | 320 | A |
| | | $T_J = 45^\circ\text{C}$, $t = 8.3\text{ms}$, 60Hz | 360 | A |
| I^2t | | $T_J = 45^\circ\text{C}$, $t = 10\text{ms}$, 50Hz | 512 | A^2s |
| | | $T_J = 45^\circ\text{C}$, $t = 8.3\text{ms}$, 60Hz | 537 | A^2s |

Diode-Rectifier Electrical and Thermal Specifications ($T_J = 25^\circ\text{C}$, unless otherwise specified)

| Symbol | Parameters | Test Conditions | Min | Typ | Max | Unit |
|-------------|---|---|-----|-----|------|---------------|
| V_F | Forward Voltage | $I_F = 15\text{A}$, $V_{GE} = 0\text{V}$, $T_J = 25^\circ\text{C}$ | | 1.0 | | V |
| | | $I_F = 15\text{A}$, $V_{GE} = 0\text{V}$, $T_J = 125^\circ\text{C}$ | | 0.9 | | V |
| I_R | Reverse Leakage Current | $V_R = 1600\text{V}$, $T_J = 25^\circ\text{C}$ | | | 50 | μA |
| | | $V_R = 1600\text{V}$, $T_J = 125^\circ\text{C}$ | | | 1 | mA |
| R_{thJCD} | Junction-to-Case Thermal Resistance (Per Diode) | | | | 1.05 | K/W |

Brake-Chopper Absolute Maximum Ratings ($T_J = 25^\circ\text{C}$, unless otherwise specified)

| Symbol | Parameters | Test Conditions | Values | Unit |
|--------------|-----------------------------------|---|----------|----------------------|
| IGBT | | | | |
| V_{CES} | Collector - Emitter Voltage | $T_J = 25^\circ\text{C}$ | 1200 | V |
| V_{GES} | Gate - Emitter Voltage | | ± 20 | V |
| I_C | DC Collector Current | $T_C = 25^\circ\text{C}$ | 25 | A |
| | | $T_C = 80^\circ\text{C}$ | 15 | A |
| I_{CM} | Repetitive Peak Collector Current | $t_p = 1\text{ms}$ | 30 | A |
| P_{tot} | Power Dissipation Per IGBT | | 105 | W |
| Diode | | | | |
| V_{RRM} | Repetitive Reverse Voltage | $T_J = 25^\circ\text{C}$ | 1200 | V |
| $I_{F(AV)}$ | Average Forward Current | $T_C = 25^\circ\text{C}$ | 15 | A |
| I_{FRM} | Repetitive Peak Forward Current | $t_p = 1\text{ms}$ | 30 | A |
| I^2t | | $T_J = 125^\circ\text{C}$, $t = 10\text{ms}$, $V_R = 0\text{V}$ | 60 | A^2s |

Brake-Chopper Electrical and Thermal Specifications ($T_J = 25^\circ\text{C}$, unless otherwise specified)

| Symbol | Parameters | Test Conditions | Min | Typ | Max | Unit |
|---------------|---|---|-------------------------|------|------|---------------|
| IGBT | | | | | | |
| $V_{GE(th)}$ | Gate - Emitter Threshold Voltage | $V_{CE}=V_{GE}, I_C=0.6\text{mA}$ | 5.0 | 5.8 | 6.5 | V |
| $V_{CE(sat)}$ | Collector - Emitter Saturation Voltage | $I_C=15\text{A}, V_{GE}=15\text{V}, T_J=25^\circ\text{C}$ | | 1.7 | 2.15 | V |
| | | $I_C=15\text{A}, V_{GE}=15\text{V}, T_J=125^\circ\text{C}$ | | 1.9 | | V |
| I_{ICES} | Collector Leakage Current | $V_{CE}=1200\text{V}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$ | | | 50 | μA |
| | | $V_{CE}=1200\text{V}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$ | | | 1 | mA |
| I_{GES} | Gate Leakage Current | $V_{CE}=0\text{V}, V_{GE}=\pm 15\text{V}, T_J=125^\circ\text{C}$ | -400 | | 400 | nA |
| R_{Gint} | Integrated Gate Resistor | | | 0 | | Ω |
| Q_{ge} | Gate Charge | $V_{CE}=600\text{V}, I_C=15\text{A}, V_{GE}=\pm 15\text{V}$ | | 0.15 | | μC |
| C_{ies} | Input Capacitance | $V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$ | | 1.1 | | nF |
| C_{res} | Reverse Transfer Capacitance | | | | 0.04 | |
| $t_{d(on)}$ | Turn - on Delay Time | $V_{CC}=600\text{V}$ $I_C=15\text{A}$ $R_G=75\Omega$ $V_{GE}=\pm 15\text{V}$ Inductive Load | $T_J=25^\circ\text{C}$ | | 90 | ns |
| | | | $T_J=125^\circ\text{C}$ | | 90 | ns |
| t_r | Rise Time | | $T_J=25^\circ\text{C}$ | | 30 | ns |
| | | | $T_J=125^\circ\text{C}$ | | 50 | ns |
| $t_{d(off)}$ | Turn - off Delay Time | | $T_J=25^\circ\text{C}$ | | 420 | ns |
| | | | $T_J=125^\circ\text{C}$ | | 520 | ns |
| t_f | Fall Time | | $T_J=25^\circ\text{C}$ | | 70 | ns |
| | | | $T_J=125^\circ\text{C}$ | | 90 | ns |
| E_{on} | Turn - on Energy | | $T_J=25^\circ\text{C}$ | | 1.5 | mJ |
| | | | $T_J=125^\circ\text{C}$ | | 2.1 | mJ |
| E_{off} | Turn - off Energy | $T_J=25^\circ\text{C}$ | | 1.1 | mJ | |
| | | $T_J=125^\circ\text{C}$ | | 1.3 | mJ | |
| I_{SC} | Short Circuit Current | $t_{psc} \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_J=125^\circ\text{C}, V_{CC}=900\text{V}$ | | 60 | | A |
| R_{thJC} | Junction-to-Case Thermal Resistance (Per IGBT) | | | | 1.2 | K/W |
| Diode | | | | | | |
| V_F | Forward Voltage | $I_F=15\text{A}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$ | | 1.65 | 2.15 | V |
| | | $I_F=15\text{A}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$ | | 1.65 | | V |
| t_{RR} | Reverse Recovery Time | $I_F=15\text{A}, V_R=600\text{V}$ $di_p/dt=-400\text{A}/\mu\text{s}$ $T_J=125^\circ\text{C}$ | | 150 | | ns |
| I_{RRM} | Max. Reverse Recovery Current | | | 16 | | A |
| E_{rec} | Reverse Recovery Energy | | | 1.1 | | mJ |
| R_{thJCD} | Junction-to-Case Thermal Resistance (Per Diode) | | | | 1.5 | K/W |

NTC Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

| Symbol | Parameters | Test Conditions | Min | Typ | Max | Unit |
|-------------|------------|------------------------|-----|------|-----|------------|
| R_{25} | Resistance | $T_c=25^\circ\text{C}$ | | 5 | | K Ω |
| $B_{25/50}$ | | | | 3375 | | K |

Figure 1: Typical Output Characteristics for IGBT Inverter

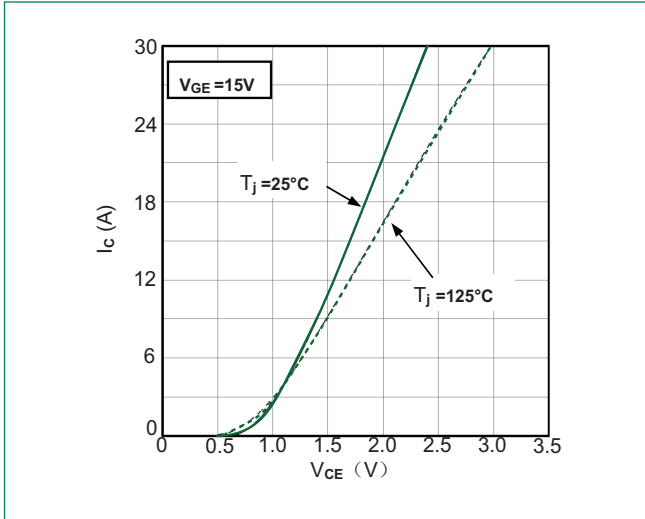


Figure 2: Typical Output Characteristics for IGBT Inverter

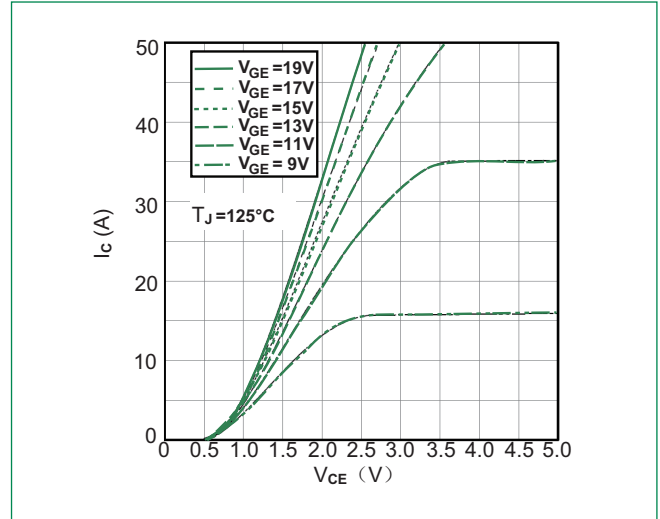


Figure 3: Typical Transfer Characteristics for IGBT Inverter

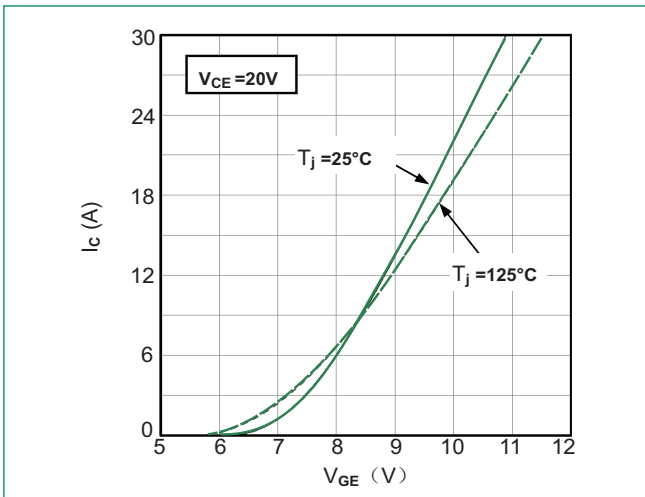


Figure 4: Switching Energy vs. Gate Resistor for IGBT Inverter

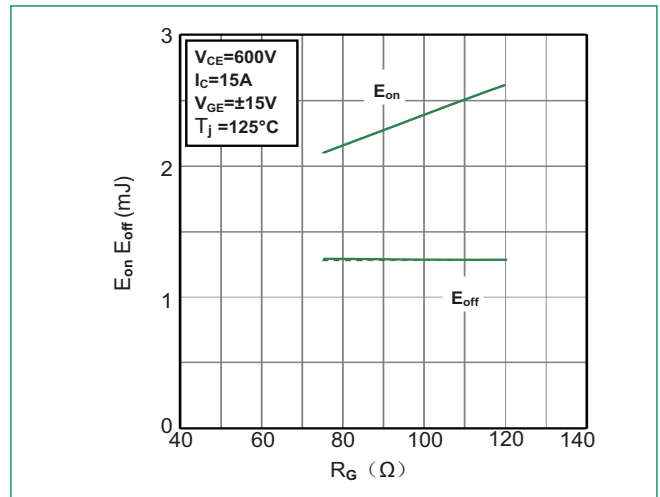


Figure 5: Switching Energy vs. Collector Current for IGBT Inverter

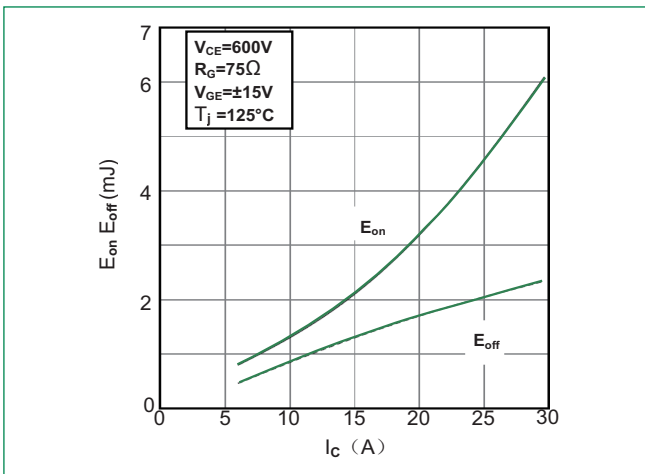


Figure 6: Reverse Biased Safe Operating Area for IGBT Inverter

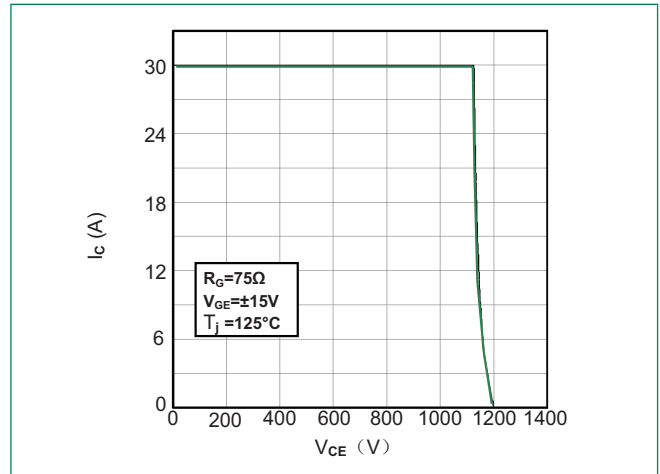


Figure 7: Diode Forward Characteristics for Diode Inverter

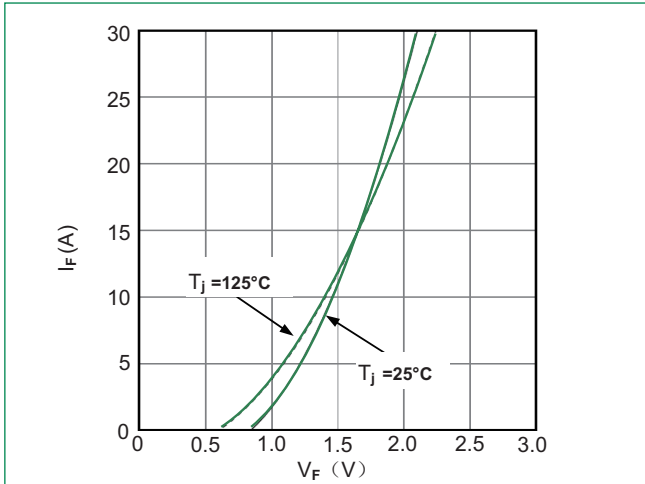


Figure 8: Switching Energy vs. Gate Resistort for Diode Inverter

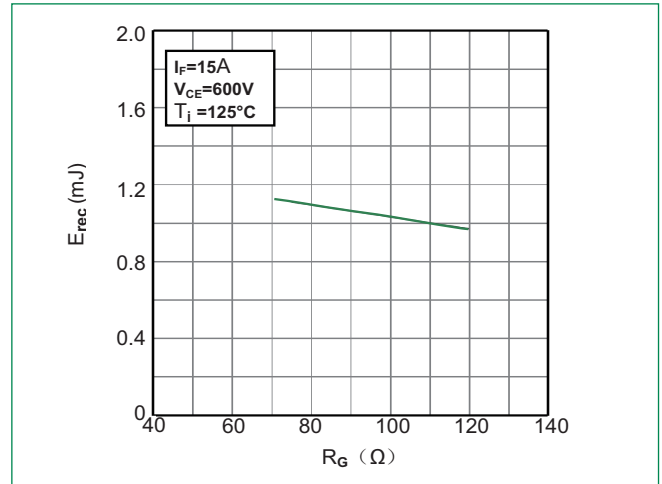


Figure 9: Switching Energy vs. Forward Current Diode-inverter

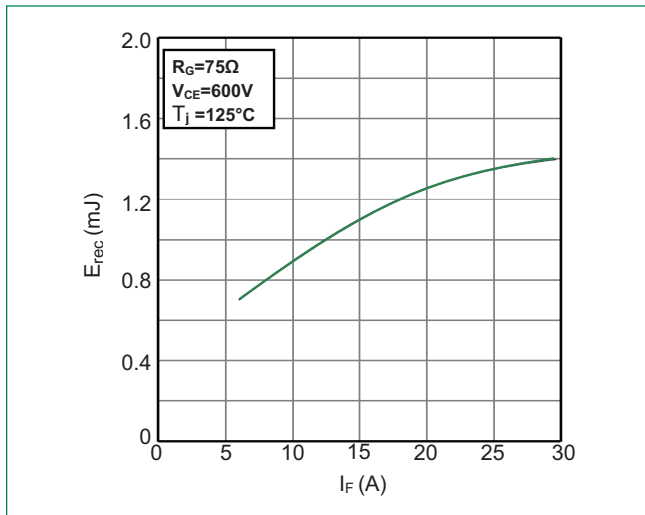


Figure 10: Transient Thermal Impedance of Diode and IGBT-inverter

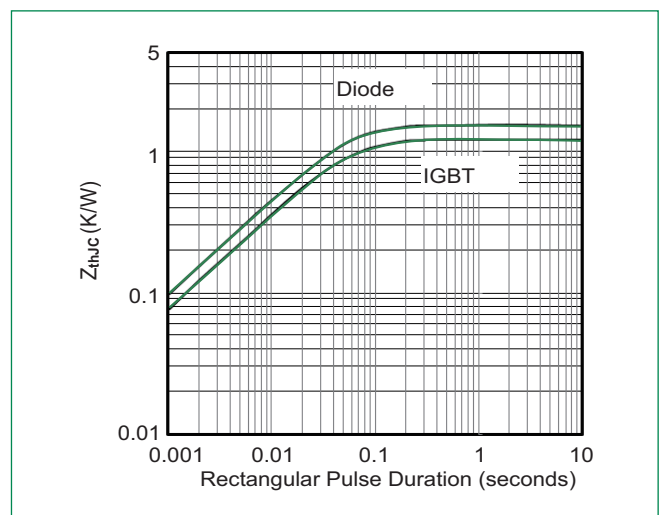


Figure 11: Diode Forward Characteristics Diode-rectifier

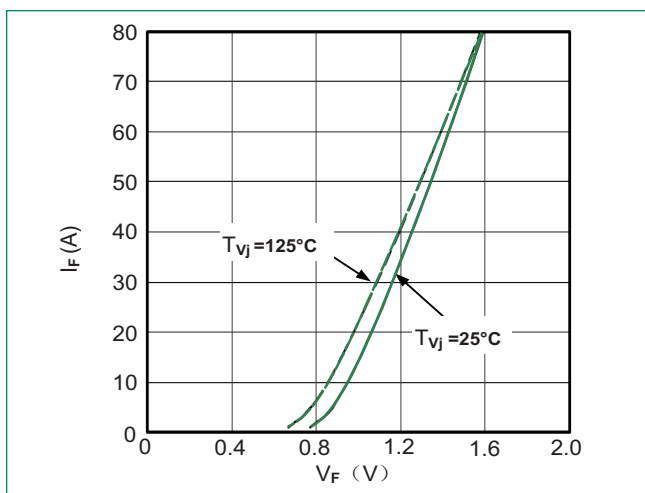


Figure 12: Typical Output Characteristics IGBT- brake chopper

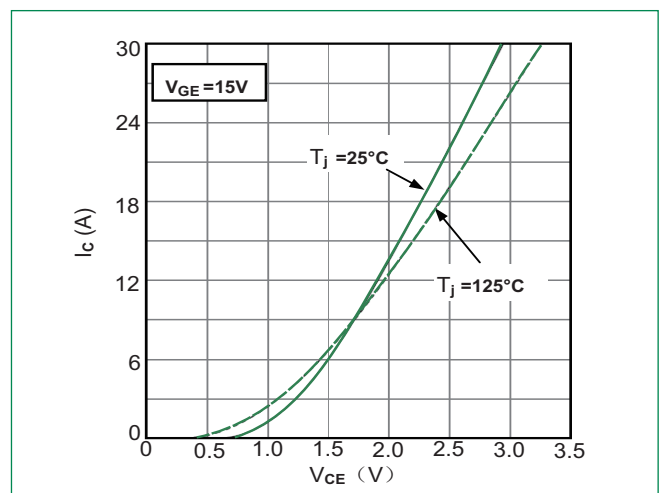


Figure 13: Diode Forward Characteristics
Diode - brake chopper

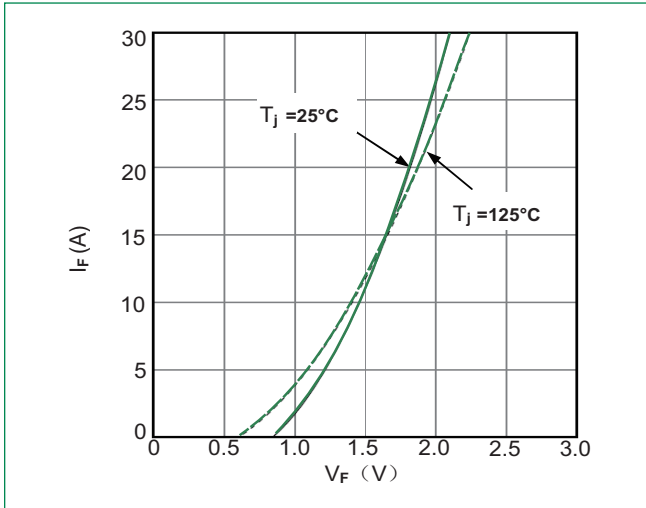
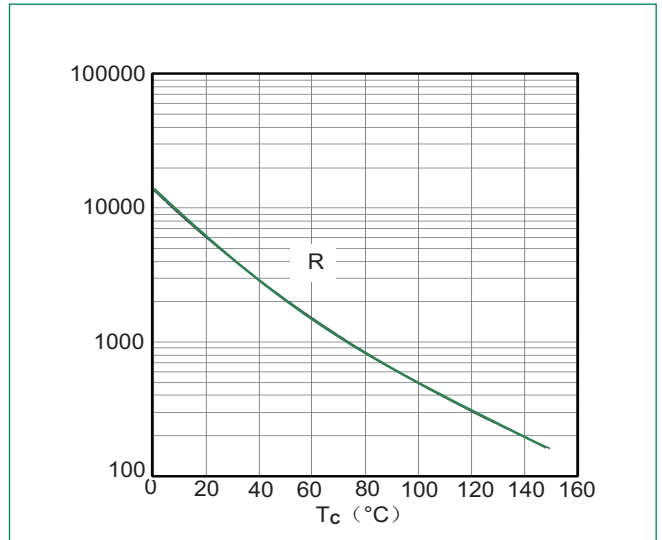
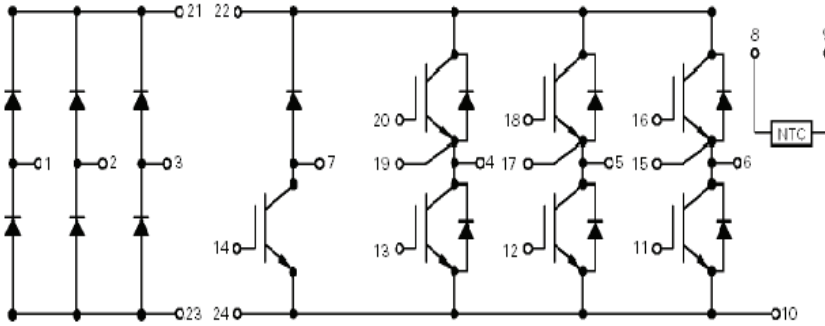


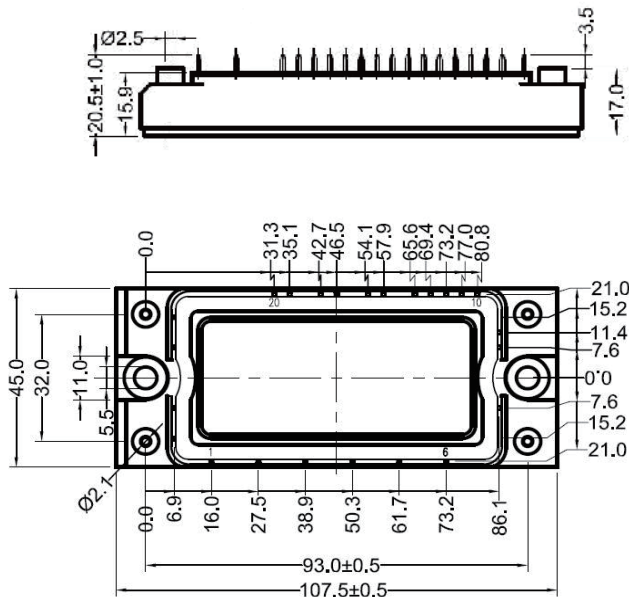
Figure 14: NTC Characteristics



Circuit Diagram



Dimensions-Package H

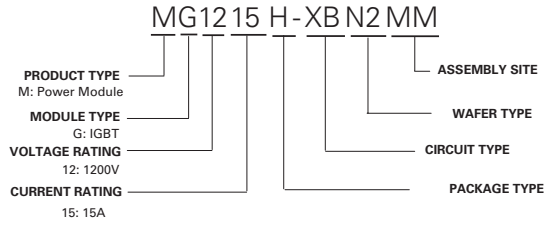


The foot pins are in gold / nickel coating

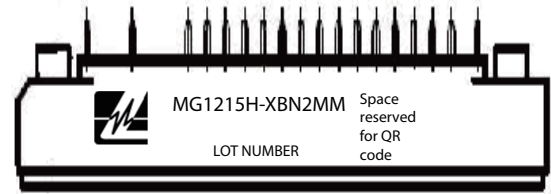
Packing Options

| Part Number | Marking | Weight | Packing Mode | M.O.Q |
|----------------|----------------|--------|--------------|-------|
| MG1215H-XBN2MM | MG1215H-XBN2MM | 180g | Bulk Pack | 40 |

Part Numbering System



Part Marking System



Компания «Океан Электроники» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Поставка оригинальных импортных электронных компонентов напрямую с производств Америки, Европы и Азии, а так же с крупнейших складов мира;
- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



JONHON

«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели,
кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



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